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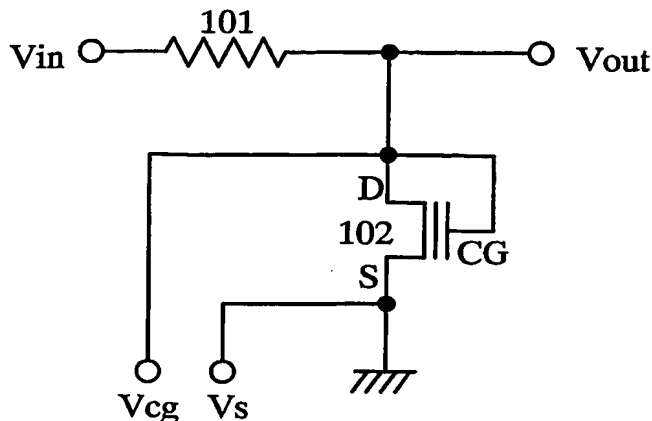
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(54) Title: LIMITER AND SEMICONDUCTOR DEVICE USING THE SAME



(57) Abstract: The limiter of the invention uses
as a diode a stacked gate thin film transistor (TFT)
including a floating gate. When the TFT includ-
ing a floating gate is used, the threshold voltage
Vth may be corrected by controlling the amount
of charge accumulated in the floating gate even in
the case where there are variations in the thresh-
old voltages Vth of the TFT.